1300/1550nm 1~4 Gbps InGaAs PIN Photodiodes Array

Part number: PY-CKmn

mxn array available (m,n=1,2,3..9,A,B,C,D,…)

Features:

- extremely low dark current, capacitance, and excellent responsivity
- *mxn* array available
- two top contacts on SI. substrate
- 250 μm array pitch, and uniform channel to channel characteristics
- extremely low electrical and optical crosstalk attenuation

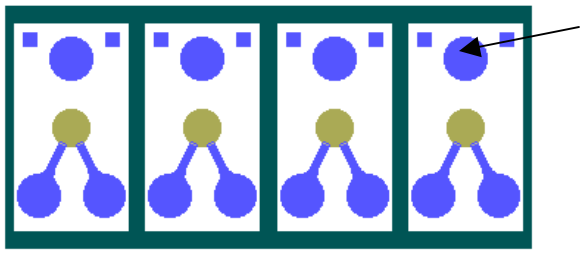
Characteristics (T=300K)

	Conditions	Min.	Typical	Max.	Unit	Notes
Bandwidth	-3 V	3			GHz	
Wavelength range		910	1310	1650	nm	
Responsivity		0.8	0.85	.95	A/W	@1310nm
Responsivity variation			2	3	%	*m*=1,*n*≤12
Dark current	-3 V		5	10	nA	
Reverse breakdown	1μA	30			V	
Capacitance	- 3 V, 1 MHz		0.40	0.55	pF	70μm window
Rise/Fall time (20%/80%)				100	ps	

Physical

	Typical	Unit	Notes
Aperture (dia.)	70	μm	
Bonding pads (dia.)	80	μm	*A-C-A-C-A-C..*
Die height	150	μm	
Die size	(*m*x460)x(*n*x250)	μm^2	*m*: rows, *n*: columns
Substrate	S.I. substrate		

Device 1x4 array layout [μm]



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